

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A method of fabricating a semiconductor device comprising:

_____ (a) preparing a semiconductor element defining a first surface and a second surface opposite the first surface, the semiconductor element having a plurality of electrodes above the first surface;

_____ (b) forming holes in the electrodes;

_____ (c) a first step of forming a through hole through holes in a the semiconductor element having a plurality of electrodes on a first surface; element, each of the through holes communicating with one of the holes; and

_____ (d) a second step of forming a conductive layer conductive layers which is are electrically connected to the electrodes and is electrodes, each of the conductive layers provided from the first surface through an inner wall of one of the through hole holes and one of the holes to a the second surface of the semiconductor element which is opposite to the first surface,

_____ wherein the conductive layer is layers being formed to have include connecting portions on the first and second surfaces so that a distance between at least two electrodes among the plurality of electrodes is different from a distance between the connecting portions on at least one of the first and second surfaces, in the second step step (d).

2. (Currently Amended) The method of fabricating a semiconductor device as defined in claim 1,

~~wherein~~ a small hole which has a diameter smaller than a diameter of the one
of the through ~~hole is~~ holes being previously formed and enlarged to form the one of the
through ~~hole~~ holes, in the ~~first step~~ step (c).

3. (Currently Amended) The method of fabricating a semiconductor device as
defined in claim 2,

~~wherein~~ a depression is being formed at a position in which the small hole is to
be formed.

4. (Currently Amended) The method of fabricating a semiconductor device as
defined in claim 2,

~~wherein~~ the small hole is being formed by a laser beam and the small hole is
being enlarged by wet etching.

5. (Canceled)

6. (Currently Amended) The method of fabricating a semiconductor device as
defined in claim 1, ~~wherein~~:

_____ the one of the through ~~hole is~~ holes being formed in an end portion of the
semiconductor element; and

_____ the connecting portions ~~are~~ being disposed in a center portion of the
semiconductor element, on the inside of the one of the through ~~hole~~ holes.

7. (Currently Amended) The method of fabricating a semiconductor device as
defined in claim 1, further ~~comprising~~ comprising:

~~a step of~~ forming a stress relieving layer on at least one of the first and second
surfaces before the ~~second step~~ step (d),

~~wherein~~ the conductive ~~layer is~~ layers being formed to reach the stress
relieving layer in the ~~second step~~ step (d).

8. (Currently Amended) The method of fabricating a semiconductor device as defined in claim 7, ~~wherein:~~

~~in the step of forming a~~ the stress relieving layer, including forming a the
stress relieving layer ~~comprises having~~ a plurality of projections; and

~~the second step, step (d) including forming the conductive layer is layers~~
~~formed~~ to reach the projections.

9. (Currently Amended) The method of fabricating a semiconductor device as defined in claim 7, ~~wherein:~~

~~in the step of forming a~~ the stress relieving layer including forming a, the
stress relieving layer ~~comprises having~~ a plurality of projections, and forming
~~—————~~ a plurality of recessed portions ~~are formed~~ between the adjacent projections;
and

~~in the second step, step (d) including forming the conductive layer is layers~~
~~formed~~ to reach the recessed portions.

10. (Canceled)

11. (Currently Amended) The method of fabricating a semiconductor device as defined in claim 7,

~~wherein~~ the connecting portions ~~are being~~ formed on the stress relieving layer.

12. (Currently Amended) The method of fabricating a semiconductor device as defined in claim 1,

~~wherein~~ a distance between adjacent connecting portions among the
connecting portions ~~is being~~ wider than a distance between adjacent electrodes among the
plurality of electrodes.

13. (Currently Amended) The method of fabricating a semiconductor device as defined in claim 1, further ~~comprising~~ comprising:

~~a step of~~ providing external terminals at the connecting portions.

14. (Currently Amended) The method of fabricating a semiconductor device as defined in claim 13,

~~wherein in the step of~~ providing the external terminals, including providing a solder is provided into a thick layer on the connecting portions to form solder balls by wet back.

15. (Currently Amended) The method of fabricating a semiconductor device as defined in claim 13,

~~wherein a solder is~~ being provided on the connecting portions by electroplating or printing.

16. (Currently Amended) The method of fabricating a semiconductor device as defined in claim 1, further ~~comprising~~ comprising:

~~a step of~~ forming a protective film over an area except at least the connecting portions after the ~~second step~~ step (d).

17. (Currently Amended) The method of fabricating a semiconductor device as defined in claim 1, further ~~comprising~~ comprising:

~~a step of~~ forming an insulating film over an area including the inner wall of the one of the through hole holes after the first step (c) and before the ~~second step~~ step (d),

~~wherein the conductive layer is~~ layers being formed on the insulating film in the ~~second step~~ step (d).

18. (Currently Amended) The method of fabricating a semiconductor device as defined in claim 17,

~~wherein the insulating film is~~ being formed by coating a resin over an area including the inner wall of the one of the through hole holes.

19. (Currently Amended) The method of fabricating a semiconductor device as defined in claim 17, ~~wherein:~~

the one of the through ~~hole is~~ holes being filled with a resin in ~~the step of~~ forming the insulating film; and

the conductive ~~layer is~~ layers being formed within the one of the through ~~hole,~~ holes, through the resin in the ~~second step.~~ step (d).

20. (Canceled)

21. (Currently Amended) The method of fabricating a semiconductor device as defined in claim 1,

~~wherein~~ the semiconductor element is being a part of a semiconductor wafer.

22. (Currently Amended) The method of fabricating a semiconductor ~~device,~~ comprising, device, comprising:

~~a step of~~ stacking semiconductor devices fabricated by the method as defined in claim 1, and electrically connecting adjacent two semiconductor devices by the conductive ~~layer.~~ layers.

23. (Currently Amended) The method of fabricating a semiconductor device, comprising the steps of: comprising:

stacking semiconductor devices fabricated by the method as defined in claim 21, and electrically connecting adjacent two semiconductor devices by the conductive ~~layer;~~ layers; and

cutting the semiconductor wafer into separate pieces.